HZM7.5FA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-616 (Z)
Rev 0
April 1, 1998

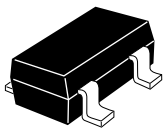
Features

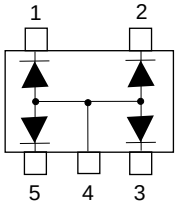
- HZM7.5FA has four devices, and can absorb external + and -surge.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM7.5FA	75A	MPAK-5

Outline





(Top View)

1 Cathode
2 Cathode
3 Cathode
4 Anode
5 Cathode

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd [*1]	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, With P.C board.

Electrical Characteristics (Ta = 25°C) [*2]

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V_Z	7.06	—	7.84	V	I_Z = 5 mA, 40ms pulse
Reverse current	I_R	—	—	2	μA	V_R = 4V
Capacitance	C	—	—	125	pF	V_R = 0V, f = 1 MHz
Dynamic resistance	r_d	—	—	30	Ω	I_Z = 5 mA
ESD-Capability [*1]	—	30	—	—	kV	C =150pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes 1. Failure criterion ; IR > 2 μA at VR = 4V.
2. Per one device.

Main Characteristic

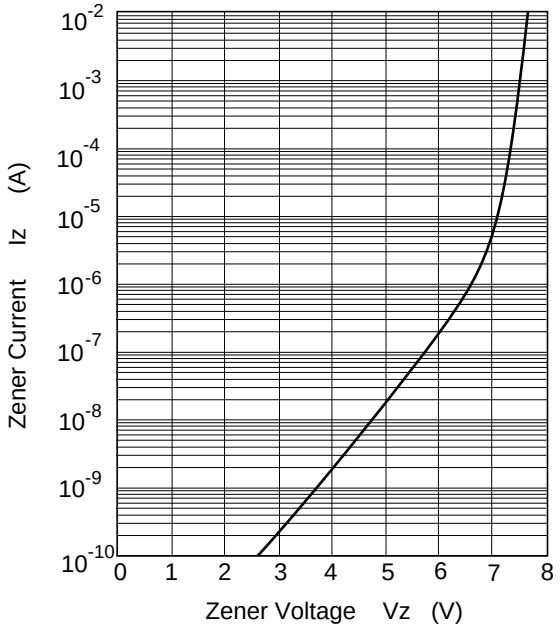


Fig.1 Zener current Vs. Zener voltage

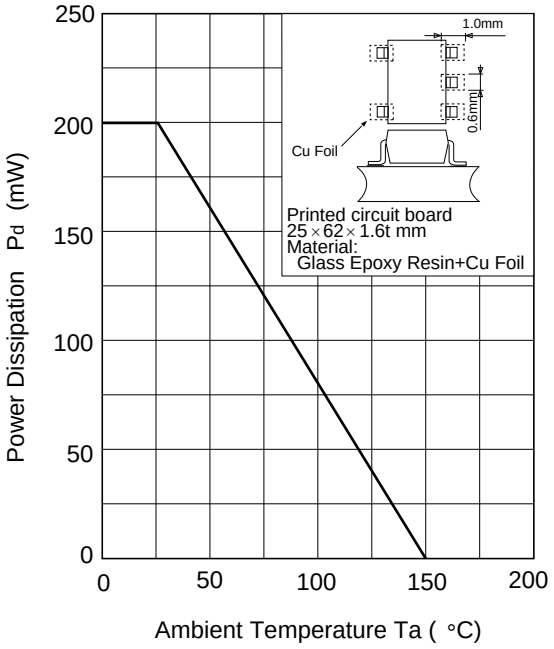


Fig.2 Power Dissipation Vs. Ambient Temperature

Main Characteristic

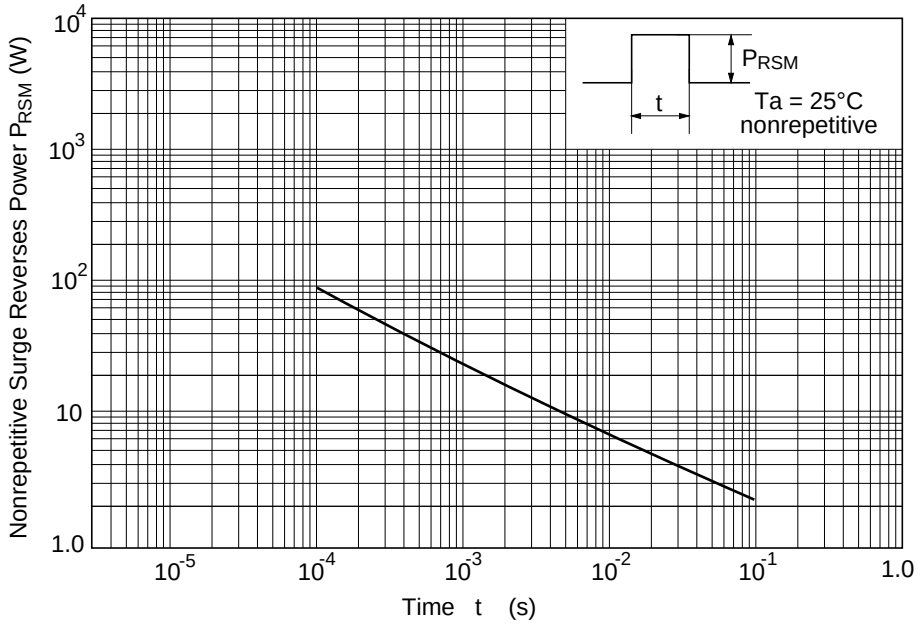


Fig.3 Surge Reverse Power Ratings

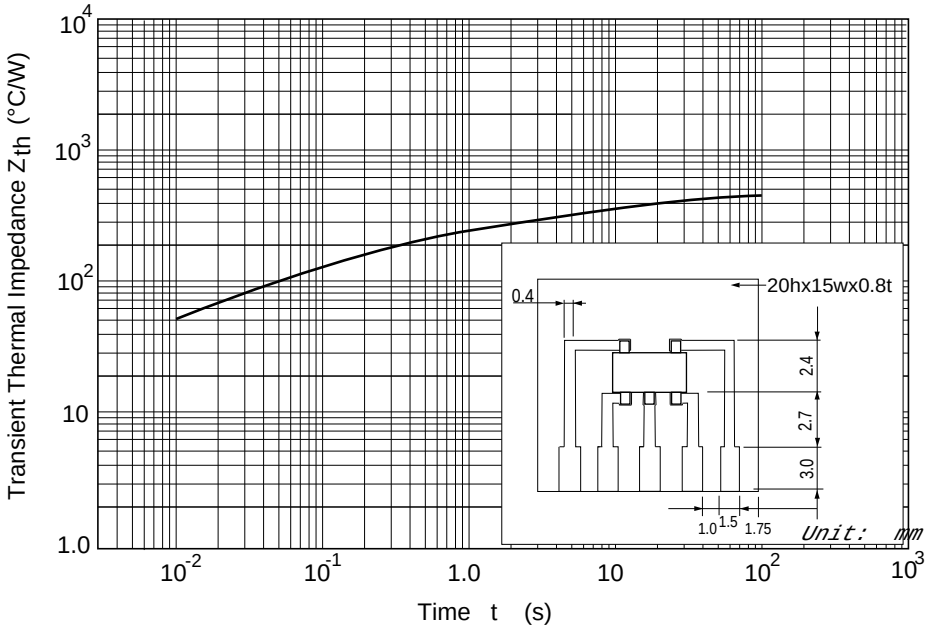
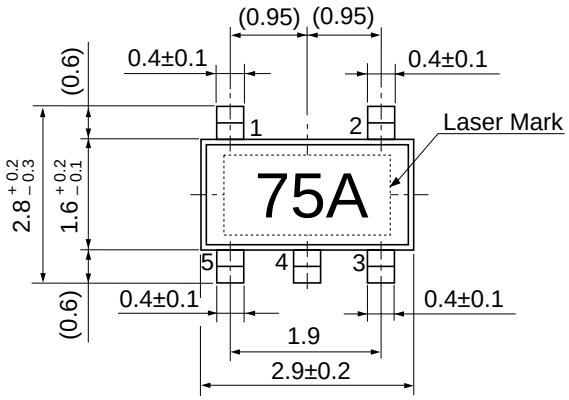
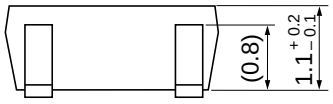
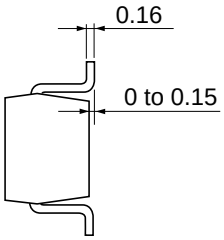


Fig.4 Transient Thermal Impedance

Package Dimensions (Unit : mm)







1 Cathode
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Hitachi Code	MPAK-5
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.013

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